

# **R5117x Series**

# 42 V Input Power Management IC with Battery Voltage Detector

No.EA-501-220310

#### OVERVIEW

The R5117x is a Power Management IC featuring input voltage range from 3.5V to 42V. This IC includes Battery Voltage Detector, SENSE Voltage Detector and 500 mA Voltage Regulator in a single chip.

#### **KEY BENEFITS**

- Reducing components and improving functional safety
- The Battery Voltage Detector suitable for Early Warning System against battery voltage reduction
- Preventing the false detection of transient characteristic fluctuations by high-speed response Voltage Regulator

#### KEY SPECIFICATIONS

- Input Voltage Range (Max. rating): 3.5 V to 42.0 V (50.0 V)
- Supply Current: Typ. 35 μA

#### Voltage Regulator (VR)

- Output Voltage Range: 3.3 V to 5.0 V
- Output Voltage Accuracy:
  - -1.25% to 0.75%(-40°C ≤Ta≤ 105°C)
- Output Current: 500 mA
- Protection:

Thermal shutdown (Detection Temp. Typ.175 °C) Output current (Typ.750 mA) Output short-circuit (Typ.105 mA)

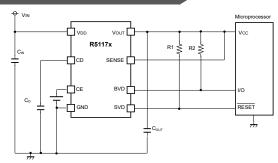
#### **SENSE Voltage Detector (SVD)**

- Detector Threshold: 2.5 V to 5.0 V (in 0.01V step)
- Detector Threshold Accuracy:
  - -1.25% to 0.75%(-40°C ≤Ta≤ 105°C)
- Release hysteresis: max 0.7%

#### **Battery Voltage Detector (BVD)**

- Detector Threshold: 3.5 V to 12.0 V (in 0.1V step)
- Detector Threshold Accuracy:
  - -2.0% to 1.0% (-40°C ≤Ta≤ 105°C)
- Release hysteresis: max 5.0%

#### TYPICAL APPLICATIONS



- C<sub>IN</sub>: 1.0μF, C<sub>OUT</sub>: 10μF, Ceramic capacitors
- C<sub>D</sub>: Ceramic capacitors for setting detection delay time

#### **SELECTION GUIDE**

Product Name	Package	Quantity per Reel
R5117SxxxA-E2-FE	HSOP-8E	1,000 pcs
R5117LxxxA-TR-FE	HQFN0808-28	2,000 pcs

xxx: Specify the set output voltage for VR (V<sub>VRSET</sub>), the set Battery voltage detector threshold (V<sub>BVSET</sub>) and the set SENSE voltage detector threshold (V<sub>SVSET</sub>) by using serial numbers starting from 001

Refer to ELECTRICAL CHARACTERISTICS for detail information.

#### **PACKAGES**







**HQFN0808-28** 8.8 x 8.8 x 0.95 (mm)

#### APPLICATIONS

- Household electric appliances such as Refrigerators, Rice Cookers and Electric Kettles
- Laptop PCs, Digital Cameras, Digital TVs, Phones and LAN Systems

No.EA-501-220310

## **SELECTION GUIDE**

The set output voltages are user-selectable options.

Product Name	Package	Quantity per Reel	Pb Free	Halogen Free
R5117SxxxA-E2-FE	SxxxA-E2-FE HSOP-8E		Yes	Yes
R5117LxxxA-TR-FE	HQFN0808-28	2,000 pcs	Yes	Yes

xxx: Specify the set output voltage for Voltage Regulator (V<sub>VRSET</sub>), the set Battery voltage detector threshold (V<sub>BVSET</sub>) and the set SENSE voltage detector threshold (V<sub>SVSET</sub>) by using serial numbers starting from 001<sup>(1)</sup>

Refer to ELECTRICAL CHARACTERISTICS for detail information

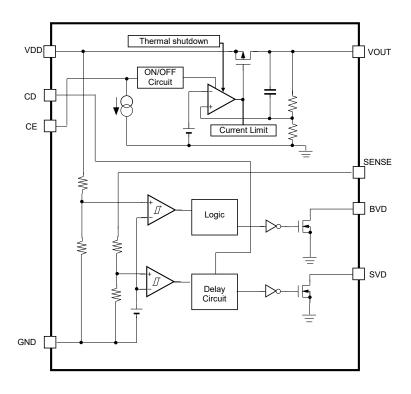
 $<sup>^{(1)}</sup>$  The combinations of  $V_{\text{VRSET}},\,V_{\text{BVSET}},\,V_{\text{SVSET}}$  are following conditions;

V<sub>VRSET</sub> = 3.3 V to 5.0 V

V<sub>BVSET</sub> = 3.5 V to 12.0 V

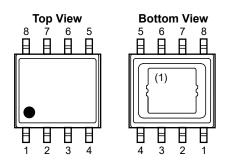
V<sub>SVSET</sub> = 2.5 V to 5.0 V

# **BLOCK DIAGRAM**



R5117xxx Block Diagram

# **PIN DESCRIPTION**

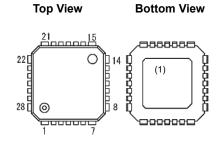


R5117S (HSOP-8E) Pin Configuration

## R5117S (HSOP-8E)

Pin No.	Symbol	Description
1	VDD	Supply Voltage Pin
2	CD	Pin for setting VD Release Output Delay Time (power-on reset time)
3	CE	Chip Enable Pin (Active-high)
4	GND	Ground Pin
5	SVD	SENSE Voltage Reduction Detection Output Pin ("Low" at detection)
6	BVD	Battery Voltage Reduction Detection Output Pin ("Low" at detection)
7	SENSE	SENSE Input Voltage Pin
8	VOUT	Regulator Output Pin

<sup>&</sup>lt;sup>(1)</sup> The tab on the bottom of the package is substrate level (GND). It is recommended that the tab be connected to the ground plane on the board.



# R5117L(HQFN0808-28) Pin Configuration

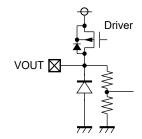
## R5117L(HQFN0808-28)

Pin No.	Symbol	Description
1	Tab (GND)	Tab
2	NC	No Connection
3	VDD	Power Supply Pin
4	VDD	Power Supply Pin
5	NC	No Connection
6	CD	Voltage Detector Reset Delay Time (Power-on Reset Time) Setting Pin
7	Tab (GND)	Tab
8	Tab (GND)	Tab
9	CE	Chip Enable Pin, Active-high
10	NC	No Connection
11	GND	Ground Pin
12	GND	Ground Pin
13	NC	No Connection
14	Tab (GND)	Tab
15	Tab (GND)	Tab
16	SVD	SENSE Voltage Reduction Detection Output Pin ("Low" at detection)
17	BVD	Battery Voltage Reduction Detection Output Pin ("Low" at detection)
18	NC	No Connection
19	SENSE	SENSE Pin
20	VOUT	Voltage Regulator Output Pin
21	Tab (GND)	Tab
22	Tab (GND)	Tab
23	NC	No Connection
24	NC	No Connection
25	NC	No Connection
26	NC	No Connection
27	NC	No Connection
28	Tab (GND)	Tab

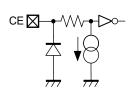
<sup>&</sup>lt;sup>(1)</sup> The tab on the bottom of the package is substrate level (GND). It is recommended that the tab be connected to the ground plane on the board.

## PIN EQUIVALENT CIRCUIT DIAGRAMS

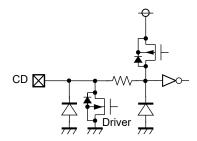
#### < VOUT Pin >



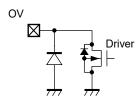
#### < CE Pin >



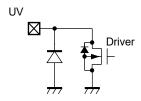
## < CD Pin >



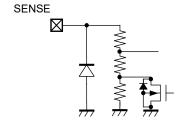
## < BVD Pin >



#### < SVD Pin >



## < SENSE Pin >



# **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Rating	Unit
\/	Input Voltage	-0.3 to 50	V
Vin	Peak Input Voltage (1)	60	V
Vce	CE Pin Input Voltage	-0.3 to 50	V
V <sub>OUT</sub>	Output Voltage	$-0.3$ to $V_{IN} + 0.3 \le 50$	V
Vsense	SENSE Pin Voltage	-0.3 to 50	V
V <sub>CD</sub>	CD Pin Output Voltage	-0.3 to 50	V
V <sub>BVD</sub>	BVD Pin Output Voltage	-0.3 to 7.0	V
Vsvd	SVD Pin Output Voltage	-0.3 to 7.0	V
PD	Power Dissipation Refer to Appendix "Pow		pation"
Tj	Junction Temperature	-40 to 125	°C
Tstg	Storage Temperature	−55 to 125	°C

#### **ABSOLUTE MAXIMUM RATINGS**

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause permanent damage and may degrade the lifetime and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings are not assured.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Rating	Unit
Vin	Input Voltage	3.5 to 42	V
Vce	CE Pin Input Voltage	0 to 42	V
V <sub>SENSE</sub>	SENSE Pin Input Voltage	0 to 6.0	V
V <sub>BVD</sub>	BVD Pin Output Voltage	0 to 6.0	V
V <sub>SVD</sub>	SVD Pin Output Voltage	0 to 6.0	V
Та	Operating Temperature	-40 to 105	°C

## **RECOMMENDED OPERATING CONDITIONS**

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

<sup>(1)</sup> Duration time: 200 ms

## **ELECTRICAL CHARACTERISTICS**

$C_{IN}$ = 1.0 $\mu$ F, $C_{OUT}$ = 10 $\mu$ F, $V_{IN}$ = 14 V, unless otherwise noted.							
The specifications surrounded by $\square$ are guaranteed by design engineering at $-40^{\circ}\text{C} \le \text{Ta} \le 105^{\circ}\text{C}$ .							

#### R5117xxxx

For All  $(Ta = 25^{\circ}C)$ 

Symbol	Parameter	Condition			Тур.	Max.	Unit
1	Supply Current	I <sub>OUT</sub> = 0 mA <sup>(1)</sup>	3.5V ≤ V <sub>BVSET</sub> < 8.0V		35	65	μA
Iss		IOUT – U IIIA (1)	8.0V ≤ V <sub>BVSET</sub> ≤ 12.0V		33	60	
Istandby	Standby Current	V <sub>IN</sub> = 14 V, V <sub>CE</sub> = 0		10	25	μA	
I <sub>PD</sub>	CE Pull-down Current				0.2	0.6	μA
VCEH	CE Input Voltage, high			2.0		42	V
$V_{CEL}$	CE Input Voltage, low			0		1.0	V

All test items listed under Electrical Characteristics are done under the pulse load condition (Tj ≈ Ta = 25°C).

VR Section  $(Ta = 25^{\circ}C)$ 

Symbol	Parameter	Co	ndition	Min.	Тур.	Max.	Unit
Vout	Output Voltage	V <sub>IN</sub> = 14 V,	Ta = 25°C	×0.995		×1.005	V
<b>V</b> 001	Output voltage	I <sub>ОUТ</sub> = 1 mA	-40°C ≤ Ta ≤ 105°C	×0.9875		×1.0075	V
ΔVουτ/	Load Regulation	V <sub>IN</sub> = V <sub>SET</sub> + 3.0 V	1 mA ≤ I <sub>OUT</sub> ≤ 300 mA	-10	0	10	m\/
$\Delta I_{OUT}$	Load Regulation	VIN - VSEI + 3.0 V	1 mA ≤ I <sub>OUT</sub> ≤ 500 mA	-15	U	15	mV
$V_{DIF}$	Dropout Voltage	І <sub>оит</sub> = 500 mA	V <sub>SET</sub> = 3.3 V		1.1	1.7	V
- 5			V <sub>SET</sub> = 5.0 V		0.9	1.5	-
ΔVουτ/	Line Regulation	I <sub>OUT</sub> = 1 mA	$8.0 \text{ V} \le V_{IN} \le 16 \text{ V}$	-10	0	10	mV
$\Delta V_{\text{IN}}$	Line Negulation	1001 - 1111A	$6.0 \text{ V} \le V_{IN} \le 32 \text{ V}$	-25	U	25	
I <sub>LIM</sub>	Output Current Limit	V <sub>IN</sub> = 8.0 V		500	750		mA
Isc	Short Current Limit	V <sub>OUT</sub> = 0 V	V <sub>OUT</sub> = 0 V			150	mA
T <sub>TSD</sub>	Thermal Shutdown Temperature	Junction Temperat	165	175		°C	
T <sub>TSR</sub>	Thermal Shutdown Release Temperature	Junction Temperat	ture	125	145		°C

All test items listed under Electrical Characteristics are done under the pulse load condition (Tj ≈ Ta = 25°C).

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<sup>(1)</sup> Supply current, Standby current are depending on VDD Voltage and battery voltage detector setting when the detector power is turned on all the time. Refer to the Supply Current data in TYPICAL CHARACTERISTICS for detail information.

## **ELECTRICAL CHARACTERISTICS**

 $C_{\text{IN}}$  = 1.0  $\mu$ F,  $C_{\text{OUT}}$  = 10  $\mu$ F,  $V_{\text{IN}}$  = 14 V, unless otherwise noted. The specifications surrounded by \_\_\_\_\_ are guaranteed by design engineering at -40°C ≤ Ta ≤ 105°C.

SVD / BVD Sections (Ta = 25°C)

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit	
\/	Battery Voltage Detector	Ta = 25°C	×0.992		×1.008	V	
V <sub>BVDET</sub>	Threshold	-40°C ≤ Ta ≤ 105°C	×0.98		×1.01	V	
\/	SENSE Voltage Detector	Ta = 25°C	×0.995		×1.005	V	
VSVDET	Threshold	-40°C ≤ Ta ≤ 105°C	×0.9875		×1.0075		
VBVHYS	Battery Voltage Threshold Hysteresis		V <sub>BVDET</sub>	V <sub>BVDET</sub> ×0.03	V <sub>BVDET</sub> ×0.05	V	
Vsvhys	SENSE Voltage Detector Threshold Hysteresis		V <sub>SVDET</sub> ×0.003	V <sub>SVDET</sub> ×0.005	V <sub>SVDET</sub> ×0.007	V	
t <sub>DELAY</sub>	Release Output Delay Time (Power-on Reset)	C <sub>D</sub> = 10 nF <sup>(1)</sup>	2	4	8	ms	
Vuvlo	UVLO Detector Threshold			1.8	2.8	V	
Vuvlohys	UVLO Detector Threshold Hysteresis			0.1	0.2	V	
$V_{BVD}$	BVD Pull-up Voltage				6.0	V	
$V_{\text{SVD}}$	SVD Pull-up Voltage				6.0	V	
I <sub>OUTBVD</sub>	Nch Output Current (BVD Output Pin)	$V_{IN} = V_{BVDET} - 0.1V, V_{DS} = 0.1 V$	0.8	2.0		mA	
I <sub>OUTSVD</sub>	Nch Output Current (SVD Output Pin)	V <sub>IN</sub> = 3.0 V, V <sub>DS</sub> = 0.1 V	0.8	2.0		mA	
ILEAKBVD	Nch Leakage Current (BVD Output Pin)	V <sub>BVD</sub> = 5.5 V			0.3	μΑ	
I <sub>LEAKSVD</sub>	Nch Leakage Current (SVD Output Pin)	V <sub>SVD</sub> = 5.5 V			0.3	μΑ	
R <sub>LCD</sub>	C <sub>D</sub> Pin Discharge Nch Tr.ON Resistance	V <sub>CE</sub> = 0 V, V <sub>CD</sub> = 0.1 V		1.2	3.0	kΩ	

All test items listed under Electrical Characteristics are done under the pulse load condition (Tj  $\approx$  Ta = 25°C).

(1) t<sub>DELAY</sub> is adjustable by only C<sub>D</sub> of SENSE Voltage Detector. t<sub>DELAY</sub> of Battery Voltage Detector is fixed internally. Refer to Release delay time data in TYPICAL CHARACTERISTICS for detail information.

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## **R5117x Product-specific Electrical Characteristics**

The specifications surrounded by \_\_\_\_ are guaranteed by design engineering at −40°C ≤ Ta ≤ 105°C

		V <sub>OUT</sub>		V <sub>OUT</sub> -40°C ≤ Ta ≤ 105°C			
<b>Product Name</b>		Ta=25°C					
	Min.	Тур.	Max.	Min.	Тур.	Max.	
R5117x001A	4.975	5.000	5.025	4.938	5.000	5.037	
R5117x002A	3.284	3.300	3.316	3.259	3.300	3.324	

		V <sub>BVDET</sub>			V <sub>BVDET</sub>			V <sub>BVHYS</sub>	
Product Name	Ta=25°C			-40°C ≤ Ta ≤ 105°C				Ta=25°C	
	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.
R5117x001A	6.647	6.700	6.753	6.566	6.700	6.767	0.06700	0.20100	0.33500
R5117x002A	5.159	5.200	5.241	5.096	5.200	5.252	0.05200	0.15600	0.26000

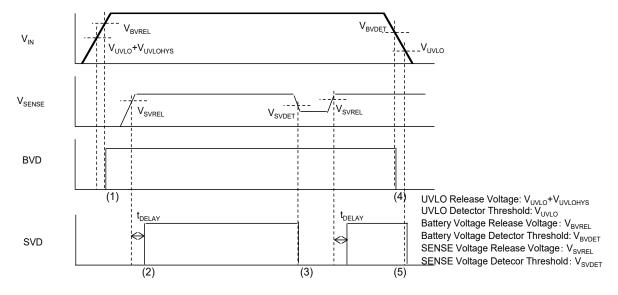
	V <sub>SVDET</sub>			V <sub>SVDET</sub>			V <sub>SVHYS</sub>		
Product Name	Ta=25°C		-40°C ≤ Ta ≤ 105°C			Ta=25°C			
	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.
R5117x001A	4.796	4.820	4.844	4.760	4.820	4.856	0.01446	0.02410	0.03374
R5117x002A	3.165	3.180	3.195	3.141	3.180	3.203	0.00954	0.01590	0.02226

## THEORY OF OPERATION

#### **Thermal Shutdown**

When the junction temperature of this device exceeds 175°C (Typ.), the built-in thermal shutdown circuit stops the regulator operation. After that, when the temperature drops to 145°C (Typ.) or lower, the regulator restarts the operation. Unless eliminating the overheating problem, the regulator turns on and off repeatedly and a pulse shaped output voltage occurs as result.

#### **R5117xxx Voltage Detector**

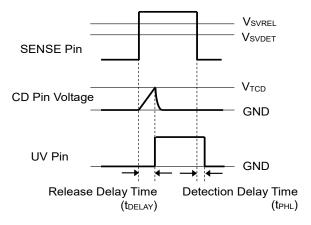


**R5117xxx Voltage Detector Timing Chart** 

- (1) When the Input pin voltage  $(V_{IN})$  exceed the Battery voltage release voltage  $(V_{BVREL})$ , the BVD pin output becomes "High" after the release delay time (Typ. 20µs).
- (2) When SENSE pin voltage (V<sub>SENSE</sub>) exceed the SENSE voltage release voltage (V<sub>SVREL</sub>), the SVD pin output becomes "High" after the release delay time (t<sub>DELAY</sub>).
- (3) When  $V_{SENSE}$  decreases less than the SENSE voltage detector threshold ( $V_{SVDET}$ ), the SVD pin output becomes "Low" after the detection delay time (Typ.100  $\mu$ s) and enters the SENSE voltage detecting state.
- (4) When the Input pin voltage (V<sub>IN</sub>) decreases less than the Battery voltage detector threshold (V<sub>BVDET</sub>), the BVD pin output becomes "Low" after the detection delay time (Typ.6.0µs) and enters the Battery voltage detecting state.
- (5) When the Input pin voltage (V<sub>IN</sub>) decreases less than the UVLO detector threshold (V<sub>UVLO</sub>), the SVD pin output becomes "Low".

# SENSE Voltage Monitoring VD Delay Operation and Release Delay Time ( $t_{\text{DELAY}}$ ) At SENSE Voltage Detection

When supplying a voltage higher than the SENSE voltage release voltage ( $V_{SVREL}$ ) to the SENSE pin, a charging to an external capacitor starts and the CD pin voltage ( $V_{CD}$ ) increases. The SVD pin voltage ( $V_{SVD}$ ) maintains "Low" until  $V_{CD}$  reaches the CD pin threshold voltage ( $V_{TCD}$ ). When  $V_{CD}$  exceeds  $V_{TCD}$ ,  $V_{SVD}$  is inverted from "Low" to "High". The release delay time ( $t_{DELAY}$ ) is the period from the time the SENSE pin voltage ( $V_{SENSE}$ ) exceeds  $V_{SVREL}$  to a rising edge of  $V_{SVD}$ . When the output voltage turns from "Low" to "High", a charge carrier of the external capacitor starts discharging. When supplying a voltage lower than the SENSE voltage detector threshold ( $V_{SVDET}$ ) to the SENSE pin, the detection delay time ( $t_{PHL}$ ) remains constant independently of the external capacitor.  $t_{PHL}$  is the period that  $V_{SVD}$  is inverted from "High" to "Low".



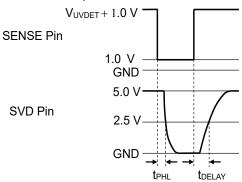
**SENSE Voltage Release Delay Timing Diagram** 

## Calculation of SENSE Voltage Release Delay Time

The following equation can calculate a typical value of the release delay time (t<sub>DELAY</sub>) with using the external capacitor (C<sub>D</sub>).

$$t_{DELAY}(s) = 0.72 \times C_D(F) / (1.8 \times 10^{-6})$$

 $t_{DELAY}$  is the period from supplying a pulse voltage of "1.0 V to (V<sub>SVDET</sub>) + 1.0 V" to the SENSE pin by pulling-up SVD pin to 5 V with 100 k $\Omega$  resistor to the SVD pins reached 2.5 V.



## **Voltage Setting of Voltage Regulator**

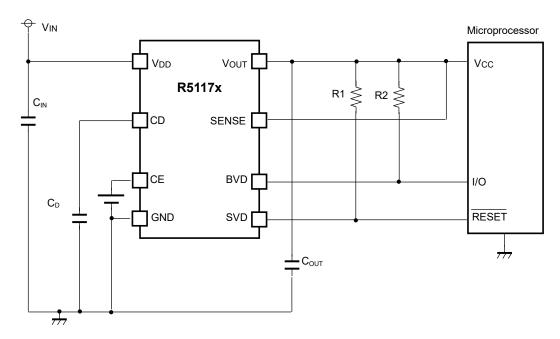
The SENSE Voltage Detector (SVD) detects the drop and rise of the Voltage Regulator (VR). When the SENSE release voltage is set to a voltage above the VR output voltage, the reset signal of SVD is not released even if SVD monitors the VR output voltage returns to the normal value after detecting the drop of VR. To prevent this issue, the following conditions are required between Vout and Vsvrel.

(VR Set Output Voltage) x  $0.9875 - 15 \text{ mV}^* > (SENSE Set Detector Threshold) x <math>1.0075 \times 1.007 \times 15 \text{mV}$  is the worst value of load regulation

When using a device without the above conditions of  $V_{\text{OUT}}$  and  $V_{\text{SVDET}}$ , careful consideration must be given to the system operation before use.

# **APPLICATION INFORMATION**

## **TYPICAL APPLICATIONS**

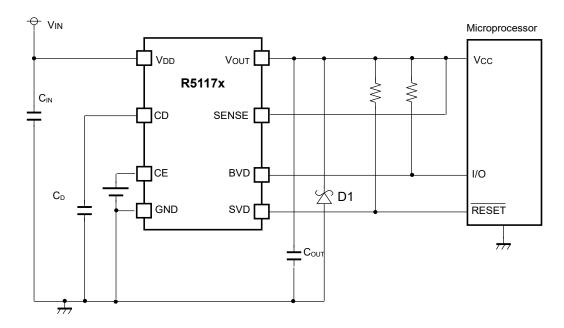


**R5117xxx TYPICAL APPLICATIONS** 

## **Recommended Components**

Symbol	Description		
C <sub>IN</sub>	Ceramic Capacitor, 1.0 μF or more, 50V Rated Voltage, CGA4J3X7R1H105K, TDK		
Соит	Ceramic Capacitor, 10 µF or more, 50V Rated Voltage, CGA4J1X7R0J106K, TDK		
C <sub>D</sub>	A capacitor corresponding to setting of Release Output Delay Time		
R1/R2	A resistor covering the output current at Nch. driver ON and the leakage current at Nch. driver OFF. Refer to "Electrical Characteristic" providing the evaluation result with using a resistor of $100k\Omega$ .		

#### TYPICAL APPLICATION FOR IC CHIP BREAKDOWN PREVENTION



R5117xxx Typical Application for IC Chip Breakdown Prevention

When a sudden surge of electrical current travels along the VOUT pin and GND due to a short-circuit, electrical resonance of a circuit involving an output capacitor (C<sub>OUT</sub>) and a short circuit inductor generates a negative voltage and may damage the device or the load devices. Connecting a schottky diode (D1) between the VOUT pin and GND has the effect of preventing damage to them.

#### **TECHNICAL NOTES**

The performance of a power source circuit using this device is highly dependent on a peripheral circuit. A peripheral component or the device mounted on PCB should not exceed a rated voltage, a rated current or a rated power. When designing a peripheral circuit, please be fully aware of the following points.

#### **Phase Compensation**

Phase compensation is provided to secure stable operation even when the load current is varied by utilizing capacity of the output ceramic capacitor and Equivalent Series Resistance (ESR). For this purpose, be sure to use a capacitor with 10  $\mu$ F or more ( $C_{OUT}$ ) and wire it to the pin as short as possible.

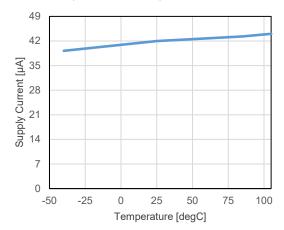
Evaluate the circuit with consideration of temperature and frequency characteristics, in case ESR value of the capacitor is large and the output is unstable. The capacitor with 1.0  $\mu$ F or more (C<sub>IN</sub>) connected in between VDD pin and GND pin must be wired the shortest.

## TYPICAL CHARACTERISTICS

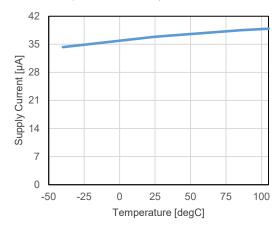
Note: Typical Characteristics are intended to be used as reference data; they are not guaranteed.

#### 1) Supply Current vs. Temperature $(V_{IN} = 14V)$

 $V_{VRSET}$  = 3.3V,  $V_{SVSET}$  = 3.0V,  $V_{BVSET}$  = 3.5V

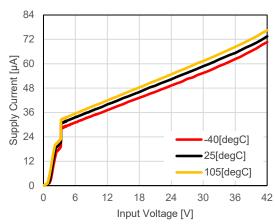


$$V_{VRSET}$$
 = 5.0V,  $V_{SVSET}$  = 4.6V,  $V_{BVSET}$  = 6.0V

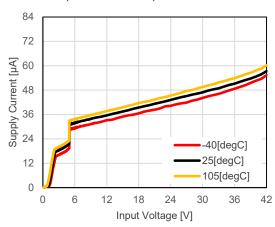


## 2) Supply Current vs. Input Voltage

 $V_{VRSET} = 3.3V$ ,  $V_{SVSET} = 3.0V$ ,  $V_{BVSET} = 3.5V$ 

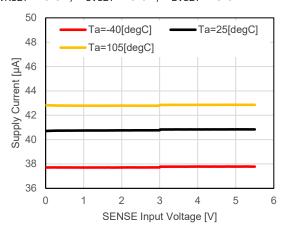


## $V_{VRSET} = 5.0V$ , $V_{SVSET} = 4.6V$ , $V_{BVSET} = 6.0V$

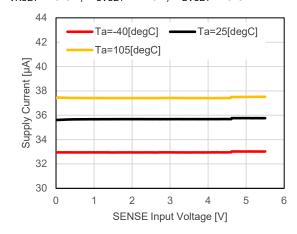


## 3) Supply Current vs. SENSE Voltage

 $V_{VRSET}$  = 3.3V,  $V_{SVSET}$  = 3.0V,  $V_{BVSET}$  = 3.5V



$$V_{VRSET} = 5.0V$$
,  $V_{SVSET} = 4.6V$ ,  $V_{BVSET} = 6.0V$ 



# 4) Output Voltage vs. Output Current ( $V_{IN}$ = $V_{VRSET}$ + 3.0 V, Ta =25 °C)

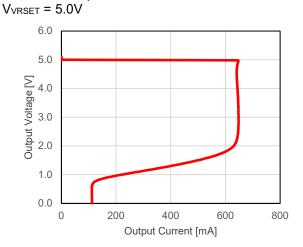
600

800

V<sub>VRSET</sub> = 3.3V

3.5
3.0

∑ 2.5
989 2.0
1.5
0 1.0
0.5



## 5) Output Voltage vs. Input Voltage (Ta =25 °C)

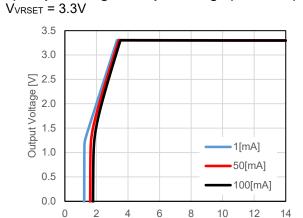
400

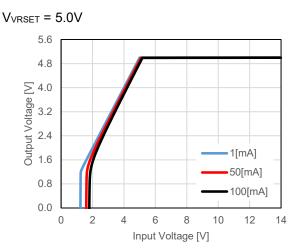
Output Current [mA]

200

0.0

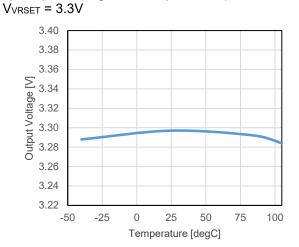
0

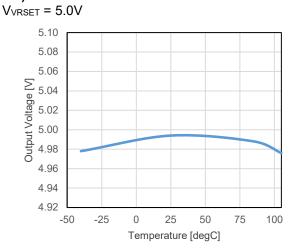




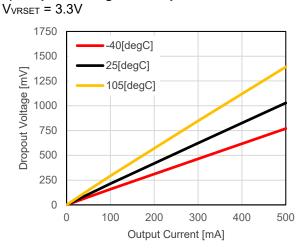
#### 6) Output Voltage vs. Temperature ( $V_{IN} = 14V$ , $I_{OUT} = 1$ mA)

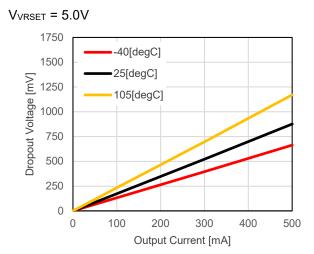
Input Voltage [V]





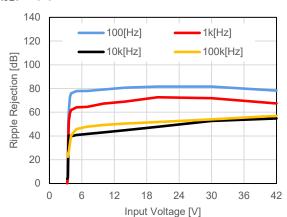
# 7) Dropout Voltage vs. Output Current

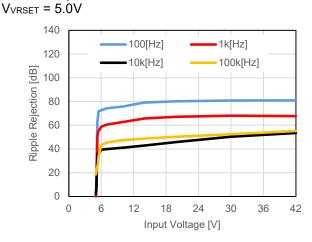




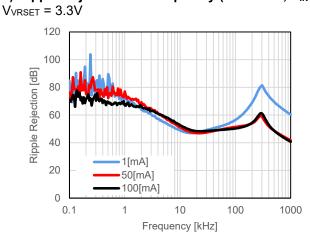
# 8) Ripple Rejection vs. Input Voltage (Ta=25 °C , Vripple = ± 0.2V)

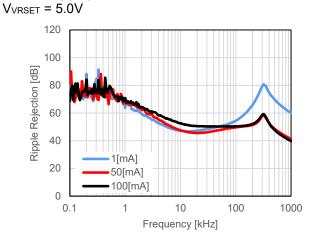
 $V_{VRSET} = 3.3V$ 





## 9) Ripple Rejection vs. Frequency (Ta=25 °C , $V_{IN}$ = 14V $\pm$ 0.2Vripple)





## 10) Input Transient Response (Ta=25 °C , $V_{IN}$ = $V_{VRSET}$ + 3.0 V $\Leftrightarrow$ $V_{VRSET}$ + 8.0 V, $I_{OUT}$ = 1 mA)

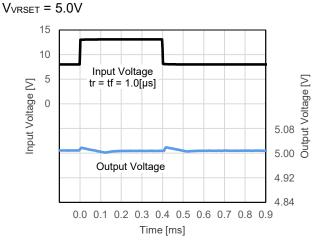
3.20

VVRSET = 3.3V

15
10
| Input Voltage | tr = tf = 1.0[µs] | 3.35 | Mark to the state of the state

0.0 0.1 0.2 0.3 0.4 0.5 0.6 0.7 0.8 0.9

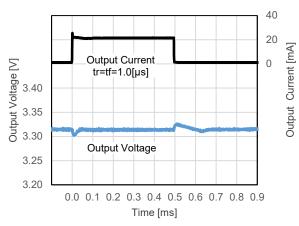
Time [ms]

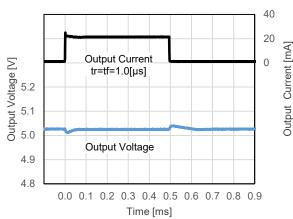


## 11) Load Transient Response (Ta=25 °C , I<sub>OUT</sub> = 1⇔20mA , V<sub>IN</sub> = 14V)

 $V_{VRSET} = 3.3V$ 



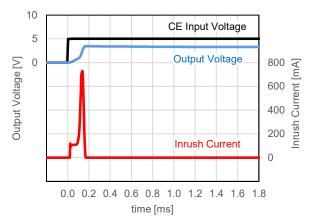


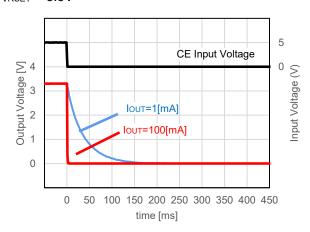


#### 12) CE Transient Response (Ta=25 °C , V<sub>IN</sub> = 14V, I<sub>OUT</sub> = 1 mA)

 $V_{VRSET} = 3.3V$ 

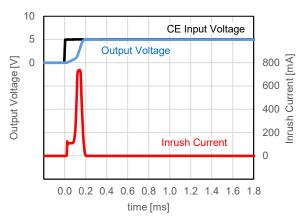




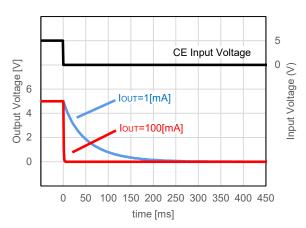


No.EA-501-220310

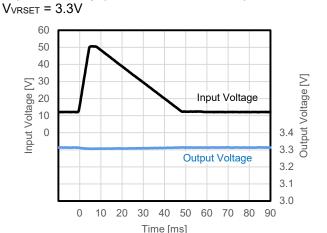




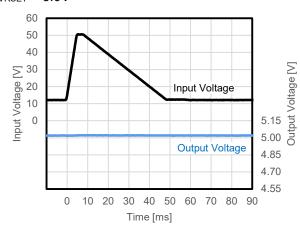
#### $V_{VRSET} = 5.0V$



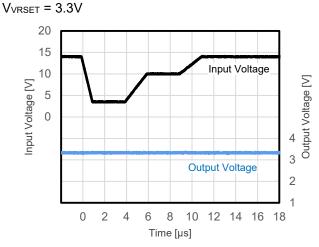
## 13) Load Dump (Ta=25 °C , $I_{OUT} = 1 \text{ mA}$ )



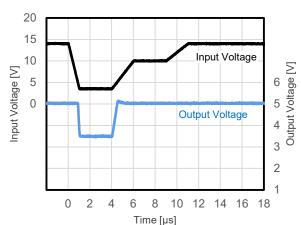
 $V_{VRSET} = 5.0V$ 



## 14) Cranking (Ta=25 $^{\circ}$ C , I<sub>OUT</sub> = 1 mA)

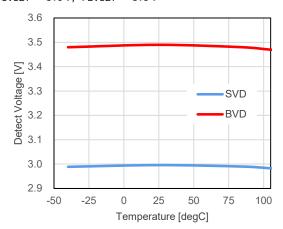


 $V_{VRSET} = 5.0V$ 

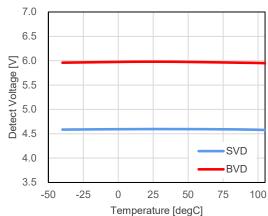


## 15) SVD/BVD Detection Voltage vs. Temperature

 $V_{SVSET} = 3.0V$ ,  $V_{BVSET} = 3.5V$ 

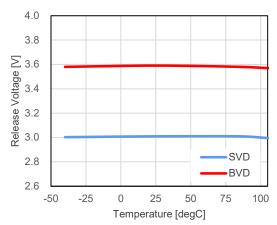


# $V_{SVSET}$ = 4.6V, $V_{BVSET}$ = 6.0V

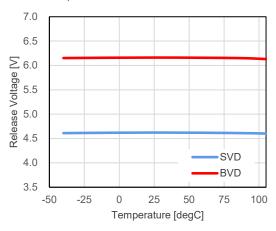


## 16) SVD/BVD Release Voltage vs. Temperature

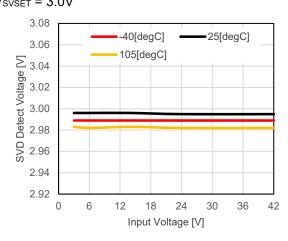
 $V_{SVSET} = 3.0V$ ,  $V_{BVSET} = 3.5V$ 



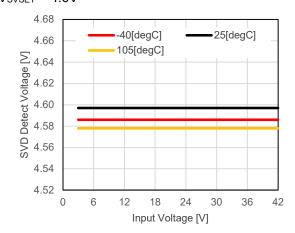
 $V_{SVSET} = 4.6V$ ,  $V_{BVSET} = 6.0V$ 



# 17) SVD Detection Voltage vs. Input Voltage $V_{\text{SVSET}}$ = 3.0V

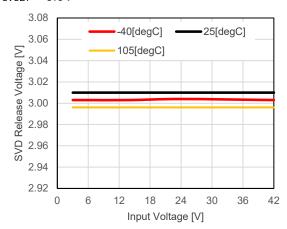


 $V_{SVSET} = 4.6V$ 

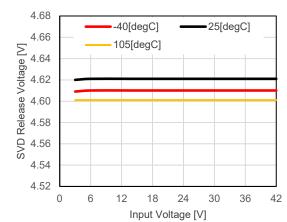


## 18) SVD Release Voltage vs. Input Voltage

 $V_{SVSET} = 3.0V$ 

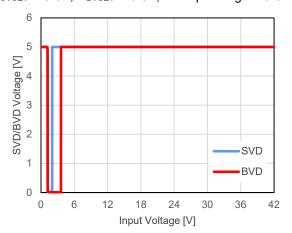


#### $V_{SVSET} = 4.6V$

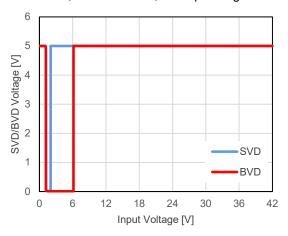


# 19) SVD/BVD Voltage vs. Input Voltage (Ta =25 °C)

V<sub>SVSET</sub> = 3.0V, V<sub>BVSET</sub> = 3.5V, Pull-up Voltage = 5.0V

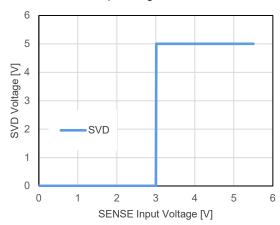


V<sub>SVSET</sub> = 4.6V, V<sub>BVSET</sub> = 6.0V, Pull-up Voltage = 5.0V

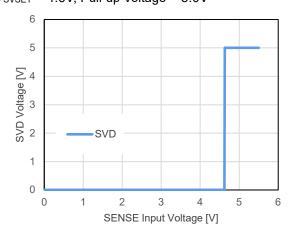


#### 20) SVD Voltage vs. SENSE Voltage (Ta =25 °C)

V<sub>SVSET</sub> = 3.0V, Pull-up Voltage = 5.0V

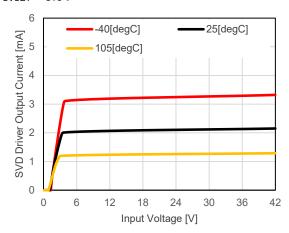


V<sub>SVSET</sub> = 4.6V, Pull-up Voltage = 5.0V

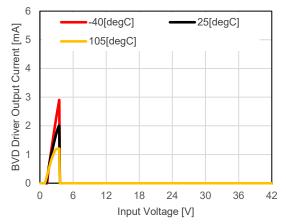


## 21) SVD/BVD Driver Output Current vs. Input Voltage

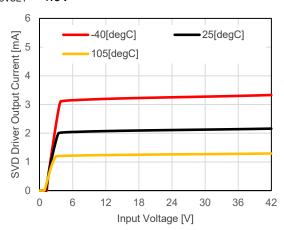
 $V_{SVSET} = 3.0V$ 



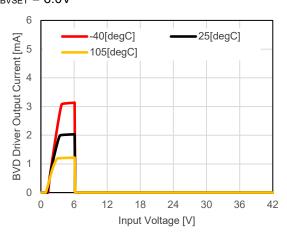
 $V_{BVSET} = 3.5V$ 



 $V_{SVSET} = 4.6V$ 

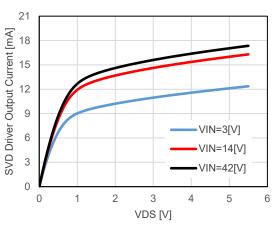


 $V_{BVSET} = 6.0V$ 

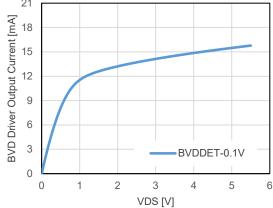


## 22) SVD/BVD Driver Output Current vs. V<sub>DS</sub> (Ta =25 °C)

 $V_{\text{SVSET}} = 4.6V$ 

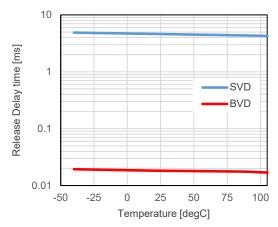


V<sub>BVSET</sub> = 6.0V



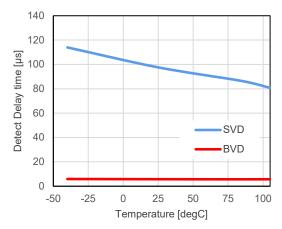
## 23) Release Delay Time vs. Temperature

 $V_{SVSET} = 4.6V$ ,  $V_{BVSET} = 6.0V$ 



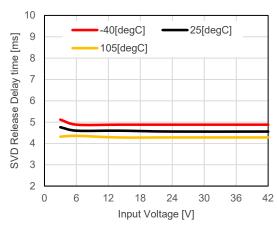
## 24) Detection Delay Time vs. Temperature

 $V_{\text{SVSET}} = 4.6 \text{V}, V_{\text{BVSET}} = 6.0 \text{V}$ 



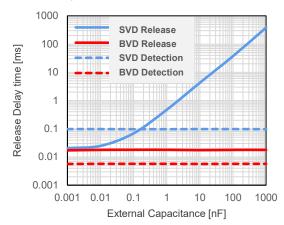
## 25) Release Delay Time vs. Input Voltage

 $V_{SVSET} = 4.6V$ 



## 26) Detection/Release Delay Time vs. External Capacitance for CD Pin (Ta =25 °C)

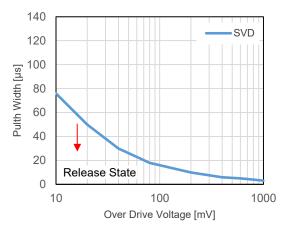
 $V_{\text{SVSET}} = 4.6V$ ,  $V_{\text{BVSET}} = 6.0V$ 



## 27) SENSE Pulse Width vs. SENSE Overdrive Voltage (Ta =25 °C)

Limit Pulse of Release State

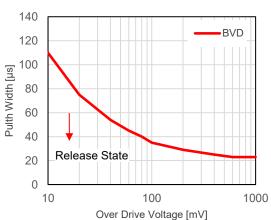
 $V_{SVSET} = 4.6V$ 



#### 28) V<sub>IN</sub> Pulse Width vs. V<sub>IN</sub> Overdrive Voltage (Ta =25 °C)

Limit Pulse of Release State

 $V_{\text{BVSET}} = 6.0V$ 



PD-HSOP-8E-(105125)-JE-A

The power dissipation of the package is dependent on PCB material, layout, and environmental conditions. The following measurement conditions are based on JEDEC STD. 51-7.

#### **Measurement Conditions**

Item	Measurement Conditions	
Environment	Mounting on Board (Wind Velocity = 0 m/s)	
Board Material	Glass Cloth Epoxy Plastic (Four-Layer Board)	
Board Dimensions	76.2 mm × 114.3 mm × 0.8 mm	
Copper Ratio	Outer Layer (First Layer): Less than 95% of 50 mm Square Inner Layers (Second and Third Layers): Approx. 100% of 50 mm Square Outer Layer (Fourth Layer): Approx. 100% of 50 mm Square	
Through-holes	φ 0.3 mm × 21 pcs	

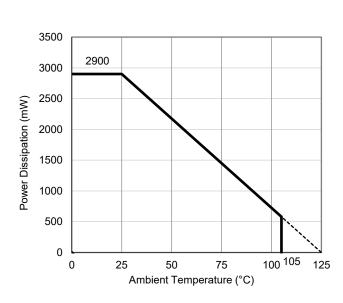
#### **Measurement Result**

 $(Ta = 25^{\circ}C, Tjmax = 125^{\circ}C)$ 

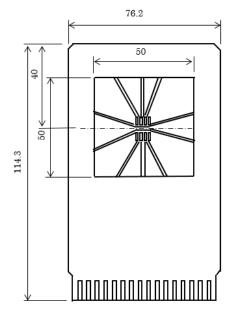
Item	Measurement Result
Power Dissipation	2900 mW
Thermal Resistance (θja)	θja = 34.5°C/W
Thermal Characterization Parameter (ψjt)	ψjt = 10°C/W

 $\theta$ ja: Junction-to-ambient thermal resistance.

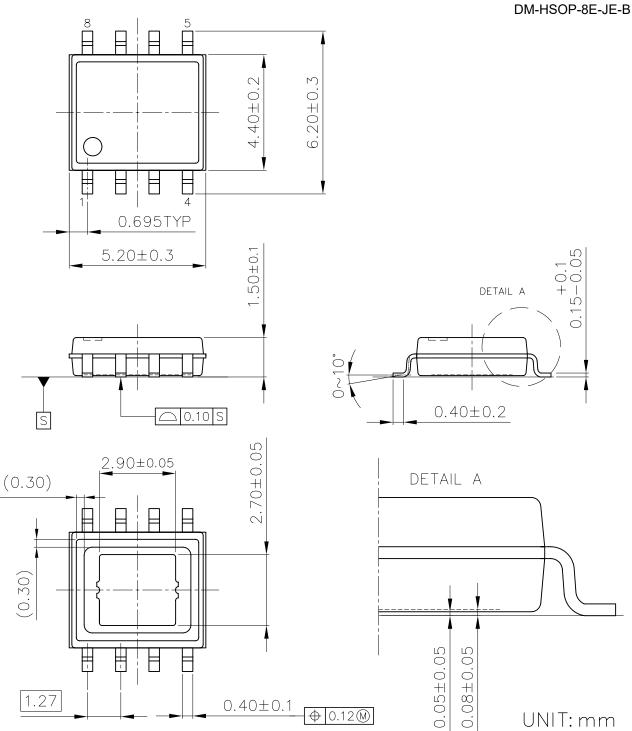
ψjt: Junction-to-top of package thermal characterization parameter



Power Dissipation vs. Ambient Temperature



**Measurement Board Pattern** 



**HSOP-8E Package Dimensions** 

PD-HQFN0808-28-(105125)-JE-A

The power dissipation of the package is dependent on PCB material, layout, and environmental conditions. The following measurement conditions are based on JEDEC STD. 51-7.

#### **Measurement Conditions**

Item	Measurement Conditions	
Environment	Mounting on Board (Wind Velocity = 0 m/s)	
Board Material	Glass Cloth Epoxy Plastic (Four-Layer Board)	
Board Dimensions	76.2 mm × 114.3 mm × 0.8 mm	
Copper Ratio	Outer Layer (First Layer): Less than 95% of 50 mm Square Inner Layers (Second and Third Layers): Approx. 100% of 50 mm Square Outer Layer (Fourth Layer): Approx. 100% of 50 mm Square	
Through-holes	φ 0.3 mm × 72 pcs	

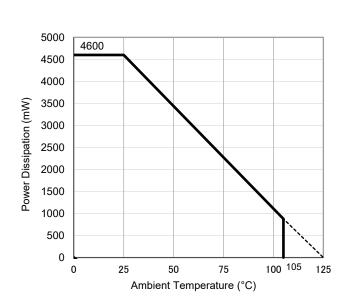
#### **Measurement Result**

 $(Ta = 25^{\circ}C, Tjmax = 125^{\circ}C)$ 

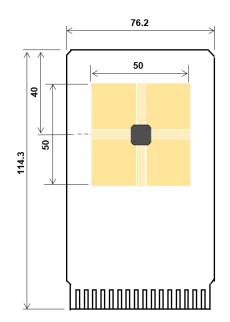
Item	Measurement Result
Power Dissipation	4600 mW
Thermal Resistance (θja)	θja = 21.5°C/W
Thermal Characterization Parameter (ψjt)	ψjt = 5°C/W

 $\theta$ ja: Junction-to-ambient thermal resistance.

ψjt: Junction-to-top of package thermal characterization parameter

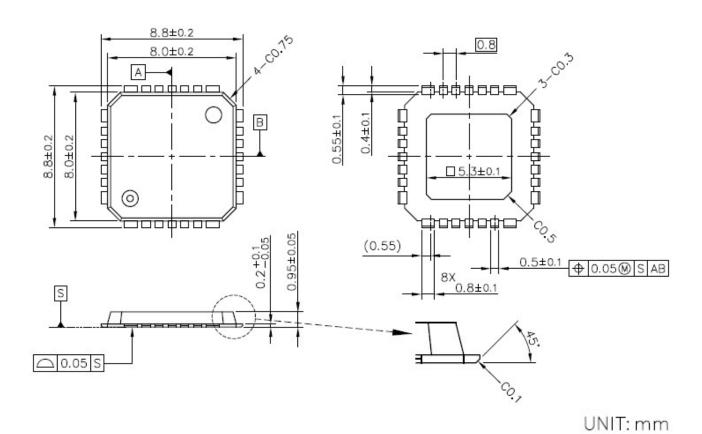


Power Dissipation vs. Ambient Temperature



**Measurement Board Pattern** 

DM-HQFN0808-28-JE-A



**HQFN0808-28 Package Dimensions** 

Nisshinbo Micro Devices Inc.

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    - When it has been proved defective due to manufacturing factors as a result of defect analysis by us, we will either deliver a substitute for the defective product or refund the purchase price of the defective product.
    - Note that such delivery or refund is sole and exclusive remedies to your company for the defective product.
  - 8-3. Remedies after Quality Warranty Period
    - With respect to any defect of this product found after the quality warranty period, the defect will be analyzed by us. On the basis of the defect analysis results, the scope and amounts of damage shall be determined by mutual agreement of both parties. Then we will deal with upper limit in Section 8-2. This provision is not intended to limit any legal rights of your company.
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